## TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

# 155184

#### ULTRA HIGH SPEED SWITCHING APPLICATION.

• Small Package : SC-59

• Low Forward Voltage : V<sub>F(3)</sub>=0.9V (Typ.)

• Fast Reverse Recovery Time :  $t_{rr} = 1.6ns$  (Typ.)

• Small Total Capacitance : C<sub>T</sub>=0.9pF (Typ.)

## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Maximum (Peak) Reverse Voltage	$v_{RM}$	85	V	
Reverse Voltage	$V_{\mathbf{R}}$	80	V	
Maximum (Peak) Forward Current	$I_{FM}$	300 (*)	mA	
Average Forward Current	IO	100 (*)	mA	
Surge Current (10ms)	$I_{FSM}$	2 (*)	A	
Power Dissipation	P	150	mW	
Junction Temperature	$T_j$	125	°C	
Storage Temperature	$ m T_{stg}$	-55~125	°C	

Unit in mm

+0.5
2.5-0.3
+0.25
+0.25
+0.25
1.5-0.15

1. ANODE
2. ANODE
3. CATHODE

JEDEC TO-236MOD

EIAJ SC-59

TOSHIBA 1-3G1F

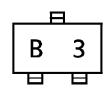
Weight: 0.012g

(\*) Unit Rating. Total Rating=Unit Rating×1.5.

### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V <sub>F (1)</sub>	I <sub>F</sub> =1mA	_	0.60	_	V
	$V_{F(2)}$	$I_{\mathbf{F}} = 10 \text{mA}$	_	0.72	_	
	V <sub>F (3)</sub>	I <sub>F</sub> =100mA	_	0.90	1.20	
Reverse Current	I <sub>R (1)</sub>	$V_R = 30V$	_	_	0.1	$\mu$ A
	$I_{R(2)}$	$V_R = 80V$	_	_	0.5	
Total Capacitance	$\mathrm{C}_{\mathrm{T}}$	$V_R=0$ , f=1MHz	_	0.9	3.0	pF
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =10mA (Fig.1)	_	1.6	4.0	ns

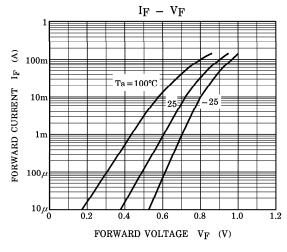
### **MARKING**

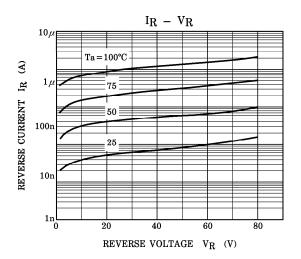


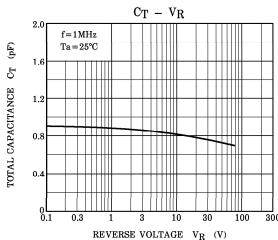
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**TOSHIBA 1SS184** 







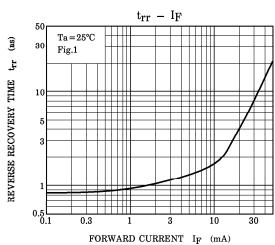
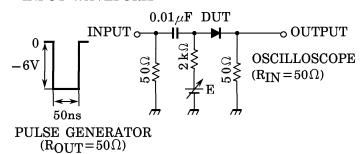
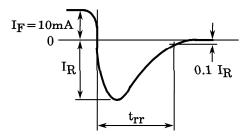


Fig.1 Reverse recovery time (t<sub>rr</sub>) test circuit

### INPUT WAVEFORM

### **OUTPUT WAVEFORM**





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